## **Magnetization-Dependent**  $T_c$  Shift in Ferromagnet/Superconductor/Ferromagnet Trilayers **with a Strong Ferromagnet**

Ion C. Moraru, W. P. Pratt, Jr., and Norman O. Birge\*

*Department of Physics and Astronomy, Michigan State University, East Lansing, Michigan 48824-2320, USA* (Received 20 June 2005; published 27 January 2006)

We have measured the superconducting transition temperature  $T_c$  of Ni/Nb/Ni trilayers when the magnetizations of the two outer Ni layers are parallel (P) and antiparallel (AP). The largest difference in  $T_c$  occurs when the Nb thickness is just above the critical thickness at which superconductivity disappears completely. We have observed a difference in  $T_c$  between the P and AP states as large as 41 mK—a significant increase over earlier results in samples with higher  $T_c$  and with a CuNi alloy in place of the Ni. Our result also demonstrates that strong elemental ferromagnets are promising candidates for future investigations of ferromagnet/superconductor heterostructures.

DOI: [10.1103/PhysRevLett.96.037004](http://dx.doi.org/10.1103/PhysRevLett.96.037004) PACS numbers: 74.45.+c, 73.43.Qt, 85.25.-j, 85.75.-d

Heterostructures composed of ferromagnetic (F) and superconducting (S) materials have attracted much theoretical and experimental attention due to the rich physics produced by the interplay between competing symmetries of the order parameters [1]. In an S/F bilayer the exchange field of the ferromagnet modulates the superconducting order parameter as it decays inside the ferromagnet over a very short distance. Kontos *et al.* [2] used tunneling spectroscopy to observe the damped oscillations of the order parameter by measuring the density of states (DOS) for different thickness ferromagnets. Ryazanov *et al.* [3] observed  $\pi$ -state Josephson coupling in an S/F/ S trilayer first by varying temperature, then later by varying the thickness of the ferromagnet [4]. Earlier, several groups [5–7] had observed oscillations in the critical temperature *T<sub>c</sub>* of S/F bilayers as a function of the ferromagnet thickness  $d_F$ . Under ideal conditions  $T_c$  oscillations arise from interference between the transmitted superconducting wave function through the S/F interface and the wave reflected from the opposite surface of the ferromagnet, although in some cases alternative explanations have been proposed [8]. In many experiments, weakly ferromagnetic alloys were used in order to reduce the size of the exchange splitting in the conduction band,  $E_{ex}$ , and thus increase the penetration length  $\xi_F$  for Cooper pairs, where  $\xi_F = \hbar v_F/2E_{\text{ex}}$  in the clean limit and  $v_F$  is the Fermi velocity of the ferromagnet [9].

An alternative way to probe the influence of a ferromagnet on a superconductor is to look for  $T_c$  variations in an F/S/F trilayer structure based on the mutual orientation of the two ferromagnet magnetizations [10,11]. This effect was observed [12] and later reproduced [13] in a  $Cu_{1-x}Ni_{x}/Nb/Cu_{1-x}Ni_{x}$  system, where a weak ferromagnet was used because it is ''less devastating to superconductivity." The largest difference in  $T_c$  observed between the antiparallel (AP) and parallel (P) states of the F-layer mutual magnetizations was only 6 mK when  $T_c$  was 2.8 K. Unlike other experiments  $[2-7]$  that require the ferromag-

net thickness to be comparable to  $\xi_F$ , however, a positive feature of this experiment is that the  $T_c$  difference is predicted to persist even for thick F layers [10,11]. Thus it proves advantageous in studying systems with strong elemental ferromagnets, which have extremely short values of  $\xi_F$ .

Experimental studies of F/S systems with strong ferromagnets are of interest because they provide new challenges to theory, which does not yet address the full complexity of the ferromagnetic state with its different DOS and  $v_F$  of the majority and minority spin bands. Furthermore, pure elemental ferromagnets are in the clean limit,  $\xi_F < l_F$  where  $l_F$  is the mean free path; this complicates use of the popular Usadel equations normally applied to the dirty limit. We are motivated to work in the limit of thick ferromagnetic layers, in anticipation of future situations where superconducting order with spintriplet symmetry is induced in a superconductor surrounded by ferromagnets with noncollinear magnetizations [14]. (When  $d_F \gg \xi_F$ , the singlet component of the order parameter is completely damped.) Lastly, we wish to understand whether, in an F/S/F system with a strong ferromagnet, a large difference in  $T_c$  between the P and AP states can be achieved, as envisioned in the proposals for a superconducting spin switch [10,11]. The Ni/Nb system has been shown to be a viable candidate for experiments on F/S systems [15,16]. In this Letter we will show that Ni/Nb/Ni trilayers exhibit a significant  $T_c$  shift depending on the mutual orientation of the magnetizations of the two Ni layers.

Sets of  $Ni(7)/Nb(d_s)/Ni(7)/Fe_{50}Mn_{50}(8)/Nb(2)$  multilayers (all thicknesses are in nm) were directly deposited onto Si substrates by magnetically enhanced triode dc sputtering in a high vacuum chamber with a base pressure in the low  $10^{-8}$  Torr and an Ar pressure of  $2.0 \times$  $10^{-3}$  Torr. The Ni thickness of 7 nm was chosen to be much longer than  $\xi_F$ , which we estimate to be 0.8 nm using  $2E_{\text{ex}} = 0.23$  eV and  $v_F = 0.28 \times 10^6$  m/s for the majority band [17]. The purpose of the FeMn is to pin the magnetization direction of the top Ni layer by exchange bias [18]. The nonsuperconducting Nb capping layer protects the FeMn from oxidation. After deposition, the samples were heated to 180 °C under vacuum, just above the blocking temperature of FeMn, and cooled in an applied field of 200 Oe in the plane of the multilayer. This procedure pins the top Ni layer while leaving the bottom Ni layer free to rotate in a small applied magnetic field.

Four-probe resistance measurements with the current in the plane of the multilayer were performed to determine  $T_c$ . Samples had lateral dimensions 4.3 mm  $\times$  1.6 mm. The  $T_c$  of each sample was defined to be the temperature at which the resistance dropped to half its normal state value. Figure 1 shows the results for  $T_c$  measurements for samples from several sputtering runs, where  $d_s$  was varied between  $16-52$  nm.  $T_c$  shows a strong dependence on the superconductor thickness close to a critical thickness,  $d_s^{\text{cr}}$ , where the sensitivity to ferromagnetism is enhanced. There is no superconductivity above 36 mK for  $d_s < d_s^{\text{cr}} \approx 16.5 \text{ nm}.$ 

The magnetic configuration of our structures was verified on simultaneously sputtered samples of larger lateral size, in a SQUID magnetometer. Figure 2 shows a plot of magnetization vs applied field *H* for a sample with  $d_s =$ 18 nm taken at 100 K. The narrow hysteresis loop near  $H = 0$  shows the switching behavior of the free Ni layer with a coercive field  $H_c = 35$  Oe. The wider loop shows switching of the pinned layer and is shifted to nonzero *H* due to the exchange bias between the top Ni layer and the FeMn. Applied fields of  $\pm 100$  Oe switch the spin valve between the P and AP configurations. The nearly zero net magnetization observed at  $-100$  Oe indicates very good AP alignment between the pinned and free Ni layers, while the nearly saturated magnetization observed at  $+100$  Oe indicates good P alignment. Similarly good alignment of the P and AP states can be achieved at low temperature. The inset to Fig. 2 shows a minor hysteresis loop with  $H_c \approx 50$  Oe taken at 2.29 K, which corresponds to the middle of the superconducting transition for this sample. We obtain the same behavior for temperatures above and below the transition temperature.

Measurements of  $T_c^{\text{P}}$  and  $T_c^{\text{AP}}$  were performed by alternating the applied field between  $+100$  and  $-100$  Oe, as the temperature was slowly decreased through the transition region. The largest shift in critical temperature,  $\Delta T_c \equiv$  $T_c^{\text{AP}} - T_c^{\text{P}}$ , should occur in samples with the Nb thickness close to  $d_s^{\text{cr}}$ . Figure 3 shows a plot of *R* vs *T* for a sample with  $d_s = 17$  nm, measured in a dilution refrigerator. Two distinct transitions are observed for P and AP alignment, with a separation in temperature  $\Delta T_c \approx 28$  mK. A second sample with  $d_s = 17$  nm showed a  $\Delta T_c \approx 41$  mK, but with a slightly broader transition centered at 0.34 K. Samples with  $d_s = 18$  nm and  $T_c$  between 2 and 3 K exhibit values of  $\Delta T_c$  of only a few mK, similar to the CuNi/Nb/CuNi samples measured previously [12,13].

The inset to Fig. 3 shows a plot of *R* vs *H* for the first  $d_s = 17$  nm sample at a temperature in the middle of the transition (0.51 K). The data clearly show well-established P and AP states at  $\pm 100$  Oe, respectively, with a difference in resistance of 1.5  $\Omega$ . Above the transition the resistance does not change perceptibly when switching from P to AP alignment. An interesting feature of the *R* vs *H* curve is the behavior of the resistance as the field is swept down from  $+150$  Oe towards  $-50$  Oe and as the field is swept up from  $-150$  Oe towards  $+50$  Oe. In both cases the resist-



FIG. 1. Critical temperature vs Nb thickness for  $Ni(7)/Nb(d_s)/Ni(7)/Fe_{50}Mn_{50}(8)/Nb(2)$  samples (all thicknesses are in nm). Different symbols represent different sputtering runs. The solid line represents the theoretical fit. Inset: Schematic cross section of the samples.



FIG. 2. Magnetization vs applied field for a  $d_s = 18$  nm sample measured at  $T = 100$  K. At  $\pm 50$  Oe the free bottom Ni layer switches while the pinned top Ni layer switches at  $-500$  Oe. Inset: minor loop measured at  $T = 2.29$  K showing the switching of the free Ni layer.



FIG. 3. Resistance vs temperature for the P and AP states of a  $d_s = 17$  nm sample measured in  $\pm 100$  Oe. Two distinct transitions are observed, with  $\Delta T_c = 28$  mK. Inset: Resistance vs applied field at  $T = 0.51$  K (dotted line in main graph).

ance increases to a value higher than that of the P state after the field passes through zero. We believe this behavior involves the breaking of the free ferromagnetic layer into domains when  $H \approx H_c$ . The domain-wall fringe fields penetrate the superconductor, thus suppressing  $T_c$  slightly and producing a higher resistance. Note that this effect is *opposite* to that observed by other groups [19,20], where inhomogeneous magnetization led to enhanced superconductivity in F/S bilayers. In those experiments, the domain size must be smaller than the superconducting coherence length so that the Cooper pairs sample multiple domains [21], and the magnetic field penetrating into the superconductor must be small.

The critical temperature of F/S/F trilayers in the P and AP states has been calculated theoretically by several groups [10,11,22–24]. Since many experiments employ ferromagnetic alloys, the usual approach involves solving the Usadel equations in the dirty limit for both the superconductor and the ferromagnet. (The dirty limit applies to S when  $l_S < \xi_{BCS} = \hbar v_S \gamma / \pi^2 k_B T_{c0}$ , and to F when  $l_F <$  $\xi_F$ , where  $l_S$  and  $l_F$  are the electron mean free paths in S and F, and  $T_{c0}$  is the transition temperature of the bulk superconductor.) In our case, however, the ferromagnetic metal is both pure and strong, thus in the clean limit  $l_F$  >  $\xi_F$ . Hence we use the theory of [11] as modified in section 3.2 of [25] to make it more appropriate for the clean limit. This theory does not, however, incorporate a full description of the majority and minority spin bands of a strong ferromagnet, with different DOS,  $v_F$ , and transmission coefficients. The expression for the normalized critical temperature of the trilayer is

$$
\ln t_c + \text{Re}\Psi\left(\frac{1}{2} + \frac{2\phi^2}{t_c(d_s/\xi_S)^2}\right) - \Psi\left(\frac{1}{2}\right) = 0,\qquad(1)
$$

where  $t_c \equiv T_c/T_{c0}$  and  $T_{c0}$  is the critical temperature of an isolated Nb film of the same thickness as the one in the trilayer. The function  $\phi$  is determined from the condition  $\phi$  tan $\phi = R$  for the P state or  $(\phi \tan \phi - R') (R' \tan \phi + R')$  $\phi$ ) –  $(R'')^2$  tan $\phi$  = 0 for the AP state, where the complex function  $R = R' + iR''$  is given by

$$
R = \frac{d_s}{\xi_S} \frac{N_{\rm F} v_{\rm F} \xi_S}{2N_{\rm S} D_{\rm S}} \frac{1}{\sqrt{1 - i\xi_{\rm F}/l_{\rm F}} + 2/T_{\rm F}}.
$$
(2)

Equation (2) is valid when the ferromagnets are thick enough so that the tanh functions in [25] can be set to 1. This assumption is validated by data on Nb/Ni bilayers [16] where oscillations in  $T_c(d_F)$  are completely damped for  $d_F > 4$  nm. The dimensionless parameters that enter into this theory are the ratios  $d_s/\xi_s$ ,  $\xi_F/l_F$ , the S/F interface transparency  $T_F$ , and the combination  $N_{\rm F}v_{\rm F}\xi_{\rm S}/2N_{\rm S}D_{\rm S}$ .  $N_{\rm F}$  and  $N_{\rm S}$  are the densities of states at the Fermi energy of the F and S layers,  $v_F$  is the Fermi velocity of the ferromagnet, and  $D<sub>S</sub>$  is the diffusion constant of the superconductor.

To avoid fitting the data with four free parameters, we follow the strategy outlined by Lazar *et al.* [8] and by Sidorenko *et al.* [16]. We determine the superconducting coherence length,  $\xi_{\rm S}$ , from measurements of the critical field vs temperature of isolated Nb films, with the magnetic field applied perpendicular to the film plane. For films in the thickness range  $20-50$  nm, the values of  $\xi_S$  are close to 6 nm, which we use for our fits [26]. From the asymptotic form of Eq. (1) as  $t_c \rightarrow 0$ , one finds  $2\phi^2/(d_s^{\text{cr}}/\xi_s)^2$  =  $1/4\gamma$ , where  $\gamma = 1.781$ . Substituting  $d_s^{\text{cr}} \approx 16.5$  nm and using Eq. (2) (while ignoring the small imaginary term), we obtain the constraint

$$
\frac{N_{\rm F}v_{\rm F}\xi_{\rm S}}{2N_{\rm S}D_{\rm S}(d_s^{\rm cr})}\frac{1}{1+2/T_{\rm F}} \approx \frac{\phi^{\rm cr}\tan\phi^{\rm cr}}{(d_s^{\rm cr}/\xi_s)} = 0.24. \tag{3}
$$

Estimates of the product  $N_F v_F$  vary substantially in the literature. From [17,27], we obtain respectively  $N_F =$  $1.77 \times 10^{48} \text{ J}^{-1} \text{ m}^{-3}$  and  $v_F = 0.28 \times 10^6 \text{ m/s}$ . Fierz *et al.* [28], however, quote  $\rho_F l_F = 0.7{\text -}2.3 \text{ f}\Omega \text{ m}^2$  for Ni, which when combined with the Einstein relation  $1/\rho_F l_F$  =  $N_F v_F e^2/3$ , implies values 3–10 times smaller for  $N_F v_F$ . Combining these values with  $N_S = 5.31 \times 10^{47} \text{ J}^{-1} \text{ m}^{-3}$ [29] and using our measured  $D_S(d_s^{\text{cr}}) = 2.8 \times 10^{-4} \text{ m}^2/\text{s}$ , we obtain  $T_F = 0.05{\text -}0.6$ . The bulk resistivity of our sputtered Ni films at 4.2 K is  $\rho_F = 33$  n $\Omega$  m, which leads to values of  $l_F$  between 7 and 70 nm, given the range in  $\rho_F l_F$ quoted above. Since the Ni used in our trilayers is thin,  $l_F$  is probably limited by surface scattering, so we use the lower estimate  $l_F = 7$  nm, hence  $\xi_F/l_F \approx 0.1$ . In fact, the fit to  $T_c(d_s)$  is quite insensitive to the values of  $T_F$  and  $\xi_F/l_F$ . We used  $\zeta_F / l_F = 0.1$  and  $T_F = 0.3$  to obtain the curve shown in Fig. 1, which fits the data remarkably well.

A more stringent test of the theory is the prediction of  $\Delta T_c$ , which depends sensitively on both  $T_F$  and  $\xi_F/l_F$ . Thickness deviations from nominal values produce scatter



FIG. 4. Symbols:  $\Delta T_c$  vs  $T_c$  for our 11 thinnest samples. The line represents a fit using  $\xi_F/l_F = 0.7$  and  $T_F = 1.0$ , values larger than our best estimates.

in plots of  $T_c$  or  $\Delta T_c$  vs  $d_s$ , therefore Fig. 4 shows a plot of  $\Delta T_c$  versus  $T_c$ . If we calculate  $\Delta T_c$  using our best estimate of  $\xi_F/l_F$  and the upper limit of  $T_F$  given above, the maximum value of  $\Delta T_c$  is only a few mK when  $T_c$  is well below 1 K—hardly visible on Fig. 4. If we relax the constraints we have placed on the parameters, and instead try to produce the best fit to the  $\Delta T_c(d_s)$  data, we find that a reasonable fit can be obtained when  $\xi_F/l_F$  is allowed to be much larger than our original estimate. Figure 4 shows a fit using  $\xi_F/l_F = 0.7$  and  $T_F = 1.0$ . Similar curves can be produced by simultaneously varying  $\xi_F/l_F$  and  $T_F$  while keeping their product nearly constant. Fitting the  $\Delta T_c$  data requires letting  $\xi_F/l_F$  exceed our estimate substantially. Our  $l_F$  estimate may be too large, because the resistivity is dominated by the longer of the majority or minority band  $l_{\rm F}$ , whereas the F/S proximity effect depends on the shorter of the two [8]. A shorter  $l_F$  is also implied by the observation of complete damping of  $T_c$  oscillations in Nb/Ni bilayers for  $d_F > 4$  nm [16]. Nevertheless, producing a reasonable fit to our  $\Delta T_c$  data entails either increasing  $\xi_F/l_F$  beyond the clean limit, or increasing  $T_F$  beyond our original estimate.

In conclusion, we have observed a large difference in  $T_c$ between the P and AP magnetic states of Ni/Nb/Ni trilayers, with  $T_c^P < T_c^{AP}$ . Recently, Ruzanov *et al.* [30] reported a  $T_c$  difference between the P and AP states of a  $Ni_{0.8}Fe_{0.2}/Nb/Ni_{0.8}Fe_{0.2}$  trilayer, but with  $T_c^P > T_c^{AP}$ . Understanding these opposing behaviors in F/S systems with strong ferromagnets will require further experiments, as well as theoretical models able to account for the complexity of real ferromagnets [31].

We are grateful to R. Loloee and J. Bass for fruitful discussions. This work was supported by NSF Grants No. DMR 9809688, No. 0405238, and by the Keck Microfabrication Facility.

\*Electronic address: birge@pa.msu.edu

- [1] For a review, see Yu. A. Izyumov, Yu. N. Proshin, and M. G. Khusainov, Phys. Usp. **45**, 109 (2002).
- [2] T. Kontos, M. Aprili, J. Lesueur, and X. Grison, Phys. Rev. Lett. **86**, 304 (2001).
- [3] V. V. Ryazanov *et al.*, Phys. Rev. Lett. **86**, 2427 (2001).
- [4] V. V. Ryazanov *et al.*, J. Low Temp. Phys. **136**, 385 (2004).
- [5] J. S. Jiang, D. Davidovic, D. H. Reich, and C. L. Chien, Phys. Rev. Lett. **74**, 314 (1995).
- [6] L. V. Mercaldo *et al.*, Phys. Rev. B **53**, 14 040 (1996).
- [7] Th. Mühge *et al.*, Phys. Rev. Lett. **77**, 1857 (1996).
- [8] L. Lazar *et al.*, Phys. Rev. B **61**, 3711 (2000).
- [9] The experiments in Refs. [2–4] were in the dirty limit, so  $\zeta_F = \sqrt{\hbar D_F/2E_{ex}}$ , where  $D_F$  is the diffusion constant.
- [10] A. I. Buzdin, A. V. Vedyayev, and N. V. Ryzhanova, Europhys. Lett. **48**, 686 (1999).
- [11] L. R. Tagirov, Phys. Rev. Lett. **83**, 2058 (1999).
- [12] J. Y. Gu *et al.*, Phys. Rev. Lett. **89**, 267001 (2002).
- [13] A. Potenza and C. H. Marrows, Phys. Rev. B **71**, 180503(R) (2005).
- [14] F.S. Bergeret, A.F. Volkov, and K.B. Efetov, Phys. Rev. B **69**, 174504 (2004).
- [15] Y. Blum, A. Tsukernik, M. Karpovski, and A. Palevski, Phys. Rev. Lett. **89**, 187004 (2002).
- [16] A. S. Sidorenko *et al.*, Ann. Phys. (N.Y.) **12**, 37 (2003).
- [17] D. Y. Petrovykh *et al.*, Appl. Phys. Lett. **73**, 3459 (1998).
- [18] J. Nogués and I.K. Schuller, J. Magn. Magn. Mater. **192**, 203 (1999).
- [19] A. Yu. Rusanov, M. Hesselberth, J. Aarts, and A. I. Buzdin, Phys. Rev. Lett. **93**, 057002 (2004).
- [20] R.J. Kinsey, G. Burnell, and M.G. Blamire, IEEE Trans. Appl. Supercond. **11**, 904 (2001).
- [21] T. Champel and M. Eschrig, Phys. Rev. B **71**, 220506(R) (2005).
- [22] C.-Y. You *et al.*, Phys. Rev. B **70**, 014505 (2004).
- [23] Ya. V. Fominov, A. A. Golubov, and M. Yu. Kupriyanov, JETP Lett. **77**, 510 (2003).
- [24] I. Baladié and A. Buzdin, Phys. Rev. B **67**, 014523 (2003).
- [25] L. R. Tagirov, Physica C (Amsterdam) **307**, 145 (1998).
- [26] From  $\xi_S = \sqrt{\hbar D_S/2\pi k_B T_{c0}}$ , we obtain  $\xi_S = 7-8$  nm for  $d_s = 20-50$  nm, where  $D_s$  is determined from resistivity measurements and  $T_{c0}$  is the critical temperature of isolated Nb films. We find  $D_S$  (m<sup>2</sup>/s) =  $1.8 \times 10^{-4} + 5.9 \times 10^{-4}$  $10^{-6}d_s$  and  $T_{c0}(K) = 9.1-43/d_s$ , with  $d_s$  in nm.
- [27] J. W. D. Connolly, Phys. Rev. **159**, 415 (1967).
- [28] C. Fierz *et al.*, J. Phys. Condens. Matter **2**, 9701 (1990).
- [29] A. R. Jani, N. E. Brener, and J. Callaway, Phys. Rev. B **38**, 9425 (1988).
- [30] A. Yu. Rusanov, S. Habraken, and J. Aarts, cond-mat/ 0509156.
- [31] B. P. Vodopyanov and L. R. Tagirov, JETP Lett. **78**, 555 (2003).